

Silicon PNP Power Transistors

2SA770 2SA771

DESCRIPTION

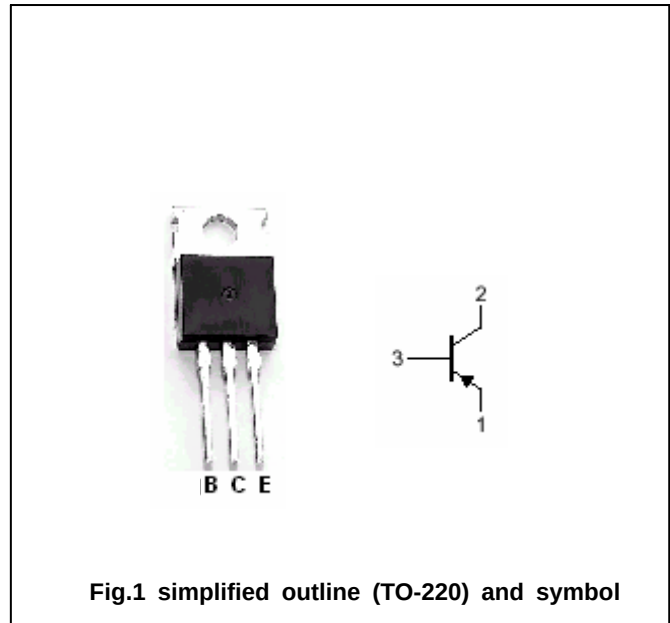
- With TO-220 package
- Complement to type 2SC1985/1986
- Low collector saturation voltage

APPLICATIONS

- For general and industrial purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA770	Open emitter	-60	V
		2SA771		-80	
V_{CEO}	Collector-emitter voltage	2SA770	Open base	-60	V
		2SA771		-80	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-6	A
I_B	Base current			-3	A
P_C	Collector power dissipation		$T_C=25^{\circ}\text{C}$	40	W
T_j	Junction temperature			150	$^{\circ}\text{C}$
T_{stg}	Storage temperature			-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA770	I _C =-25mA, I _B =0	-60			V
		2SA771		-80			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-3A; I _B =-0.3A			-1.0	V
I _{CBO}	Collector cut-off current	2SA770	V _{CB} =-60V; I _E =0			-1.0	mA
		2SA771	V _{CB} =-80V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-6V; I _C =0			-1.0	mA
h _{FE}	DC current gain		I _C =-1A; V _{CE} =-4V	40			
f _T	Transition frequency		I _C =-0.5A; V _{CE} =-12V		10		MHz

Switching times

t _r	Rise time	I _C =-3A; V _{CC} =-9V I _{B1} =-I _{B2} =-0.4A; R _L =3 Ω		0.9		μ s
t _{stg}	Storage time			1.0		μ s
t _f	Fall time			0.1		μ s

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PACKAGE OUTLINE

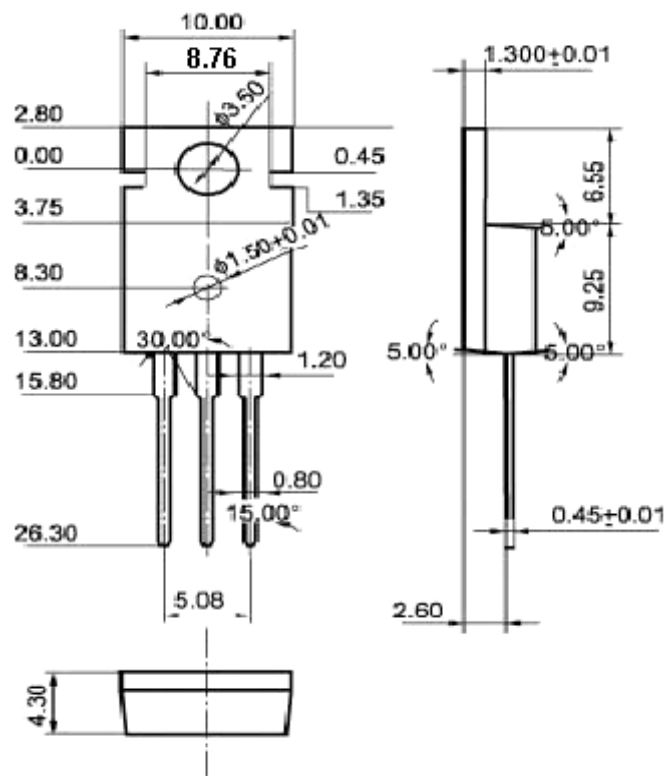


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)